

# SGW6N60UFD

## Ultra-Fast IGBT

### General Description

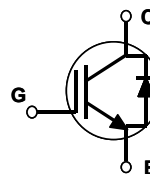
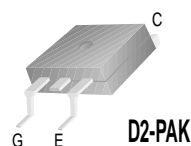
Fairchild's UFD series of Insulated Gate Bipolar Transistors (IGBTs) provides low conduction and switching losses. The UFD series is designed for applications such as motor control and general inverters where high speed switching is a required feature.

### Features

- High speed switching
- Low saturation voltage :  $V_{CE(sat)} = 2.1 \text{ V @ } I_C = 3\text{A}$
- High input impedance
- CO-PAK, IGBT with FRD :  $t_{rr} = 35\text{ns (typ.)}$

### Applications

AC & DC motor controls, general purpose inverters, robotics, and servo controls.



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	SGW6N60UFD	Units
$V_{CES}$	Collector-Emitter Voltage	600	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 20$	V
$I_C$	Collector Current @ $T_C = 25^\circ\text{C}$	6	A
	Collector Current @ $T_C = 100^\circ\text{C}$	3	A
$I_{CM(1)}$	Pulsed Collector Current	25	A
$I_F$	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	4	A
$I_{FM}$	Diode Maximum Forward Current	25	A
$P_D$	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	30	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	12	W
$T_J$	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

**Notes :**

(1) Repetitive rating : Pulse width limited by max. junction temperature

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction-to-Case	--	4.0	$^\circ\text{C/W}$
$R_{\theta JC}$ (DIODE)	Thermal Resistance, Junction-to-Case	--	7.0	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (PCB Mount) (2)	--	40	$^\circ\text{C/W}$

**Notes :**

(2) Mounted on 1" square PCB (FR4 or G-10 Material)

### Electrical Characteristics of the IGBT T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
BV <sub>CES</sub>	Collector-Emitter Breakdown Voltage	V <sub>GE</sub> = 0V, I <sub>C</sub> = 250uA	600	--	--	V
ΔBV <sub>CES</sub> /ΔT <sub>J</sub>	Temperature Coefficient of Breakdown Voltage	V <sub>GE</sub> = 0V, I <sub>C</sub> = 1mA	--	0.6	--	V/°C
I <sub>CES</sub>	Collector Cut-Off Current	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0V	--	--	250	uA
I <sub>GES</sub>	G-E Leakage Current	V <sub>GE</sub> = V <sub>GES</sub> , V <sub>CE</sub> = 0V	--	--	± 100	nA

### On Characteristics

V <sub>GE(th)</sub>	G-E Threshold Voltage	I <sub>C</sub> = 3mA, V <sub>CE</sub> = V <sub>GE</sub>	3.5	4.5	6.5	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 3A, V <sub>GE</sub> = 15V	--	2.1	2.6	V
		I <sub>C</sub> = 6A, V <sub>GE</sub> = 15V	--	2.6	--	V

### Dynamic Characteristics

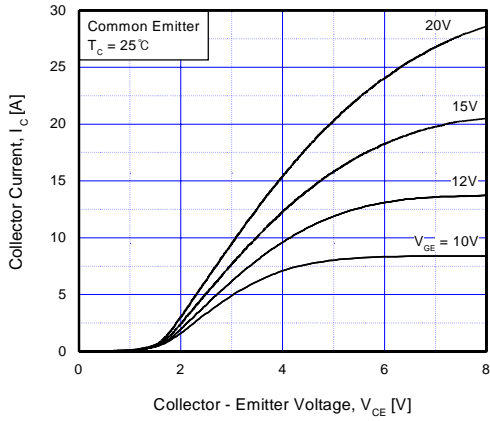
C <sub>ies</sub>	Input Capacitance	V <sub>CE</sub> = 30V, V <sub>GE</sub> = 0V, f = 1MHz	--	220	--	pF
C <sub>oes</sub>	Output Capacitance		--	22	--	pF
C <sub>res</sub>	Reverse Transfer Capacitance		--	7	--	pF

### Switching Characteristics

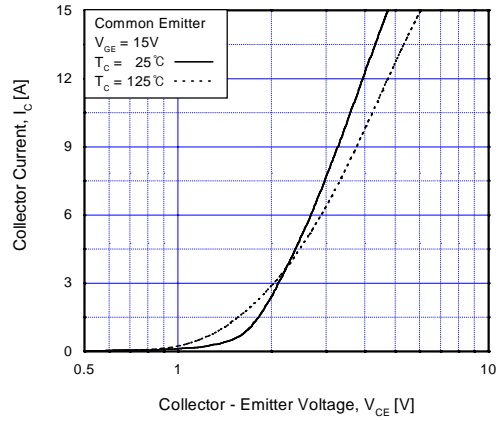
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>CC</sub> = 300 V, I <sub>C</sub> = 3A, R <sub>G</sub> = 80Ω, V <sub>GE</sub> = 15V, Inductive Load, T <sub>C</sub> = 25°C	--	15	--	ns
t <sub>r</sub>	Rise Time		--	25	--	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	60	130	ns
t <sub>f</sub>	Fall Time		--	70	150	ns
E <sub>on</sub>	Turn-On Switching Loss		--	57	--	uJ
E <sub>off</sub>	Turn-Off Switching Loss		--	25	--	uJ
E <sub>ts</sub>	Total Switching Loss	--	82	120	uJ	
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>CC</sub> = 300 V, I <sub>C</sub> = 3A, R <sub>G</sub> = 80Ω, V <sub>GE</sub> = 15V, Inductive Load, T <sub>C</sub> = 125°C	--	22	--	ns
t <sub>r</sub>	Rise Time		--	32	--	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	80	200	ns
t <sub>f</sub>	Fall Time		--	122	300	ns
E <sub>on</sub>	Turn-On Switching Loss		--	65	--	uJ
E <sub>off</sub>	Turn-Off Switching Loss		--	46	--	uJ
E <sub>ts</sub>	Total Switching Loss	--	111	170	uJ	
Q <sub>g</sub>	Total Gate Charge	V <sub>CE</sub> = 300 V, I <sub>C</sub> = 3A, V <sub>GE</sub> = 15V	--	15	22	nC
Q <sub>ge</sub>	Gate-Emitter Charge		--	5	8	nC
Q <sub>gc</sub>	Gate-Collector Charge		--	4	6	nC
L <sub>e</sub>	Internal Emitter Inductance	Measured 5mm from PKG	--	7.5	--	nH

### Electrical Characteristics of DIODE T<sub>C</sub> = 25°C unless otherwise noted

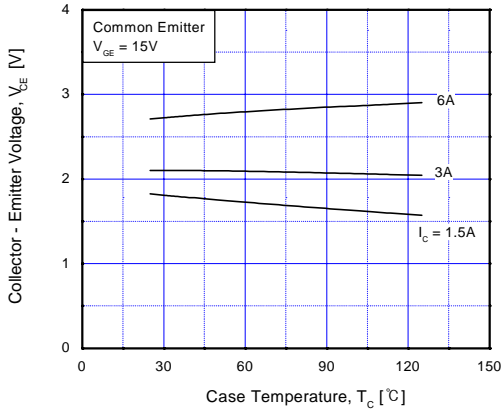
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units	
V <sub>FM</sub>	Diode Forward Voltage	I <sub>F</sub> = 4A	T <sub>C</sub> = 25°C	--	1.4	1.7	V
			T <sub>C</sub> = 100°C	--	1.3	--	
t <sub>rr</sub>	Diode Reverse Recovery Time	I <sub>F</sub> = 4A, di/dt = 200A/us	T <sub>C</sub> = 25°C	--	35	52	ns
			T <sub>C</sub> = 100°C	--	53	--	
I <sub>rr</sub>	Diode Peak Reverse Recovery Current	I <sub>F</sub> = 4A, di/dt = 200A/us	T <sub>C</sub> = 25°C	--	3.5	5.0	A
			T <sub>C</sub> = 100°C	--	4.5	--	
Q <sub>rr</sub>	Diode Reverse Recovery Charge	I <sub>F</sub> = 4A, di/dt = 200A/us	T <sub>C</sub> = 25°C	--	60	135	nC
			T <sub>C</sub> = 100°C	--	120	--	



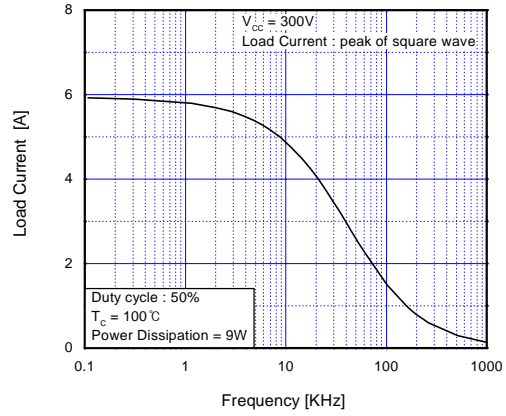
**Fig 1. Typical Output Characteristics**



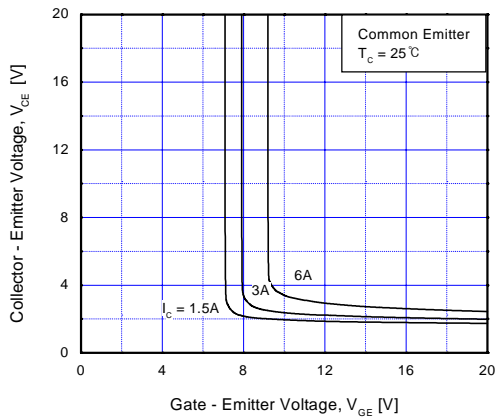
**Fig 2. Typical Saturation Voltage Characteristics**



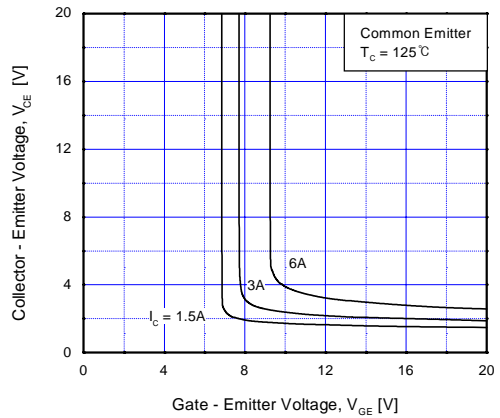
**Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level**



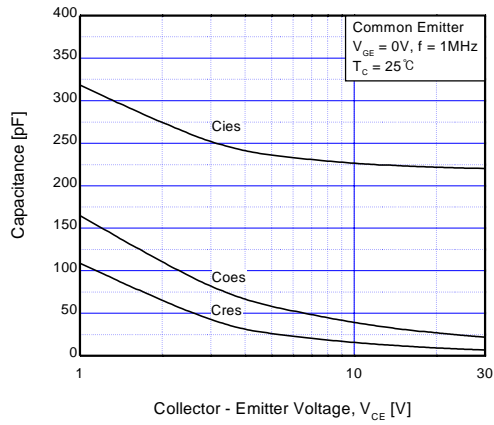
**Fig 4. Load Current vs. Frequency**



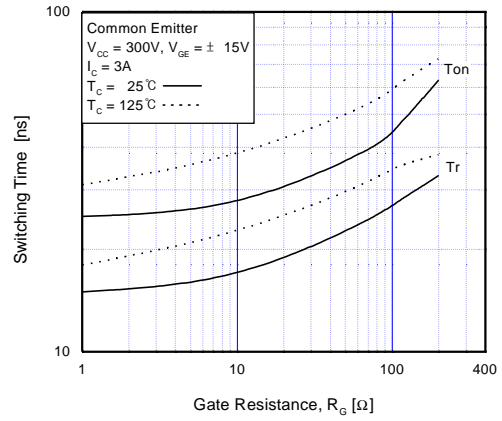
**Fig 5. Saturation Voltage vs.  $V_{GE}$**



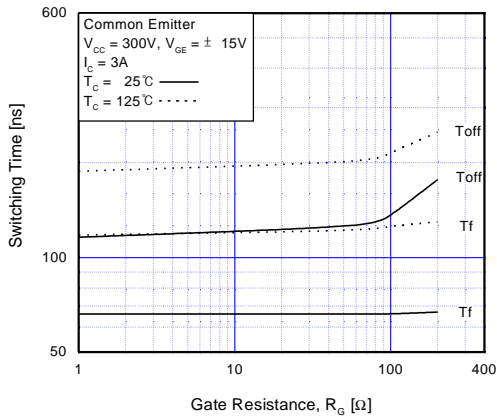
**Fig 6. Saturation Voltage vs.  $V_{GE}$**



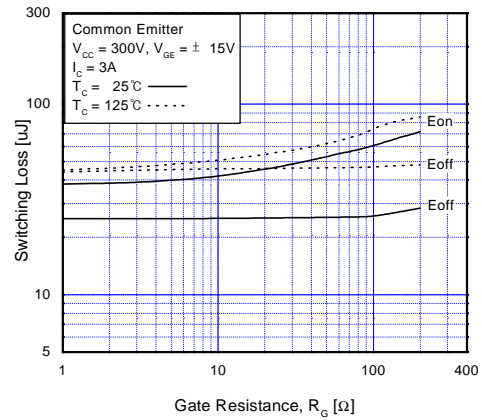
**Fig 7. Capacitance Characteristics**



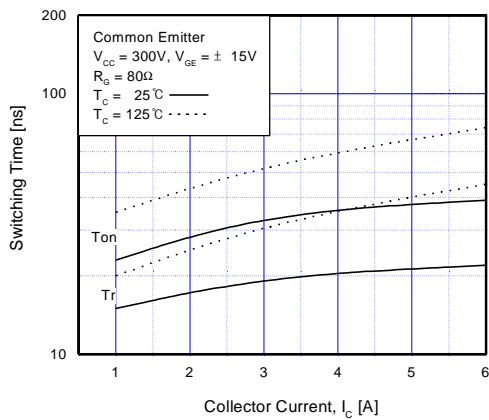
**Fig 8. Turn-On Characteristics vs. Gate Resistance**



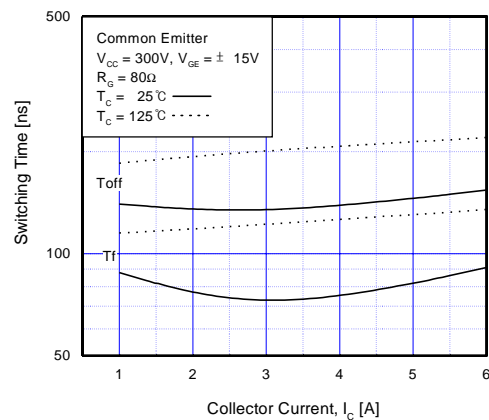
**Fig 9. Turn-Off Characteristics vs. Gate Resistance**



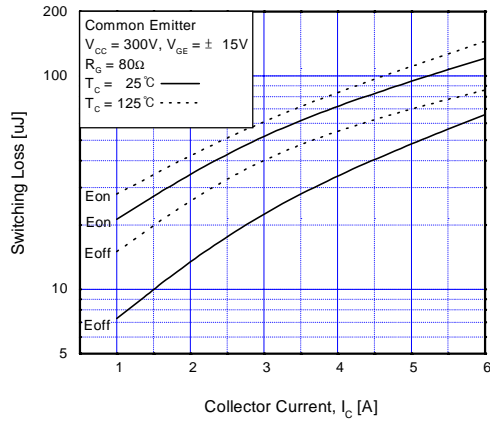
**Fig 10. Switching Loss vs. Gate Resistance**



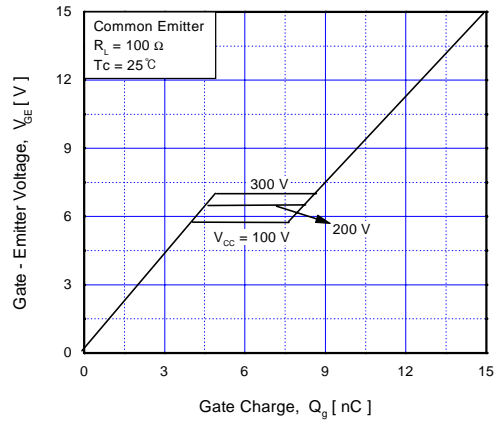
**Fig 11. Turn-On Characteristics vs. Collector Current**



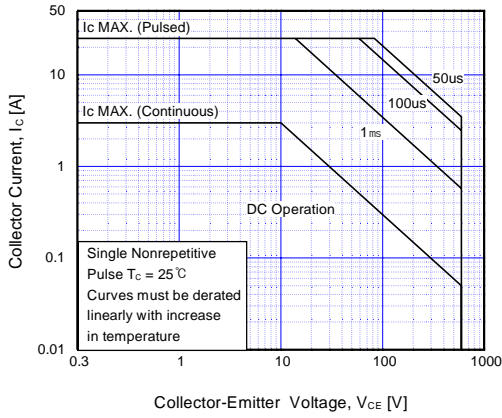
**Fig 12. Turn-Off Characteristics vs. Collector Current**



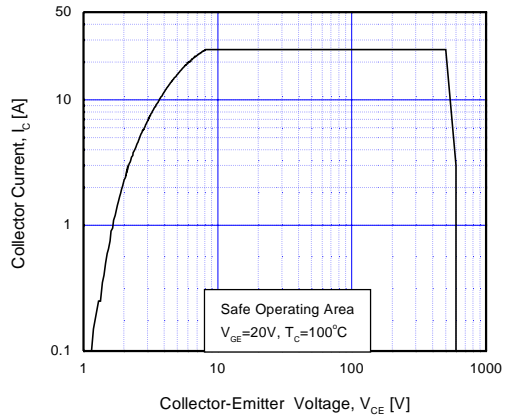
**Fig 13. Switching Loss vs. Collector Current**



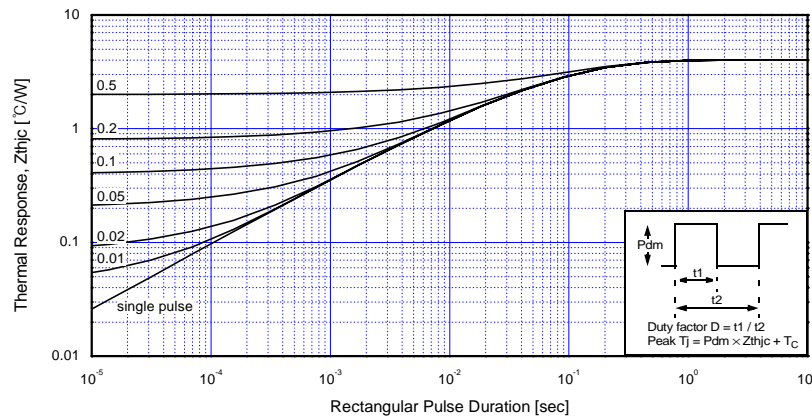
**Fig 14. Gate Charge Characteristics**



**Fig 15. SOA Characteristics**



**Fig 16. Turn-Off SOA Characteristics**



**Fig 17. Transient Thermal Impedance of IGBT**

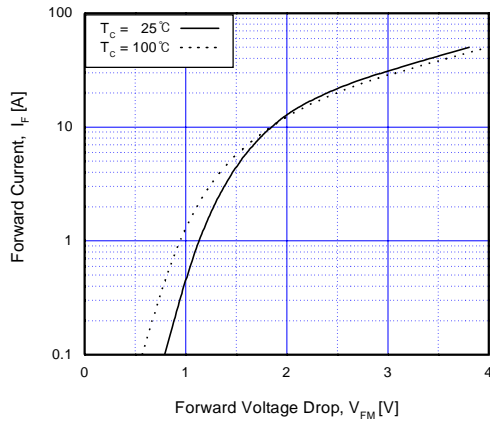


Fig 18. Forward Characteristics

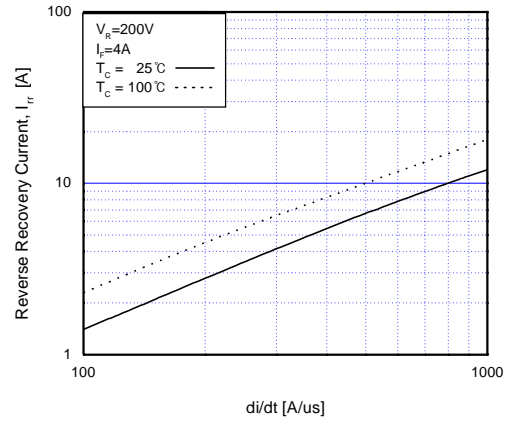


Fig 19. Reverse Recovery Current

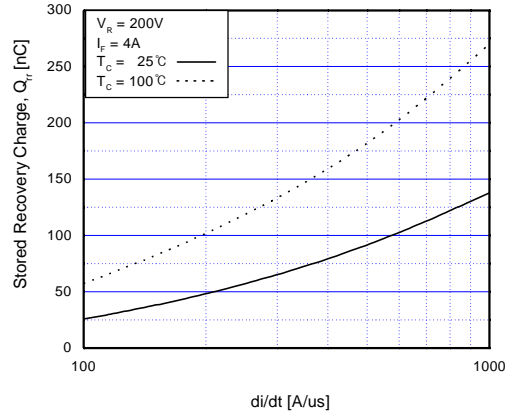


Fig 20. Stored Charge

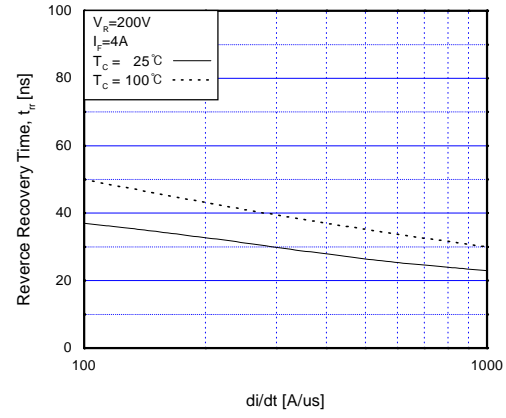
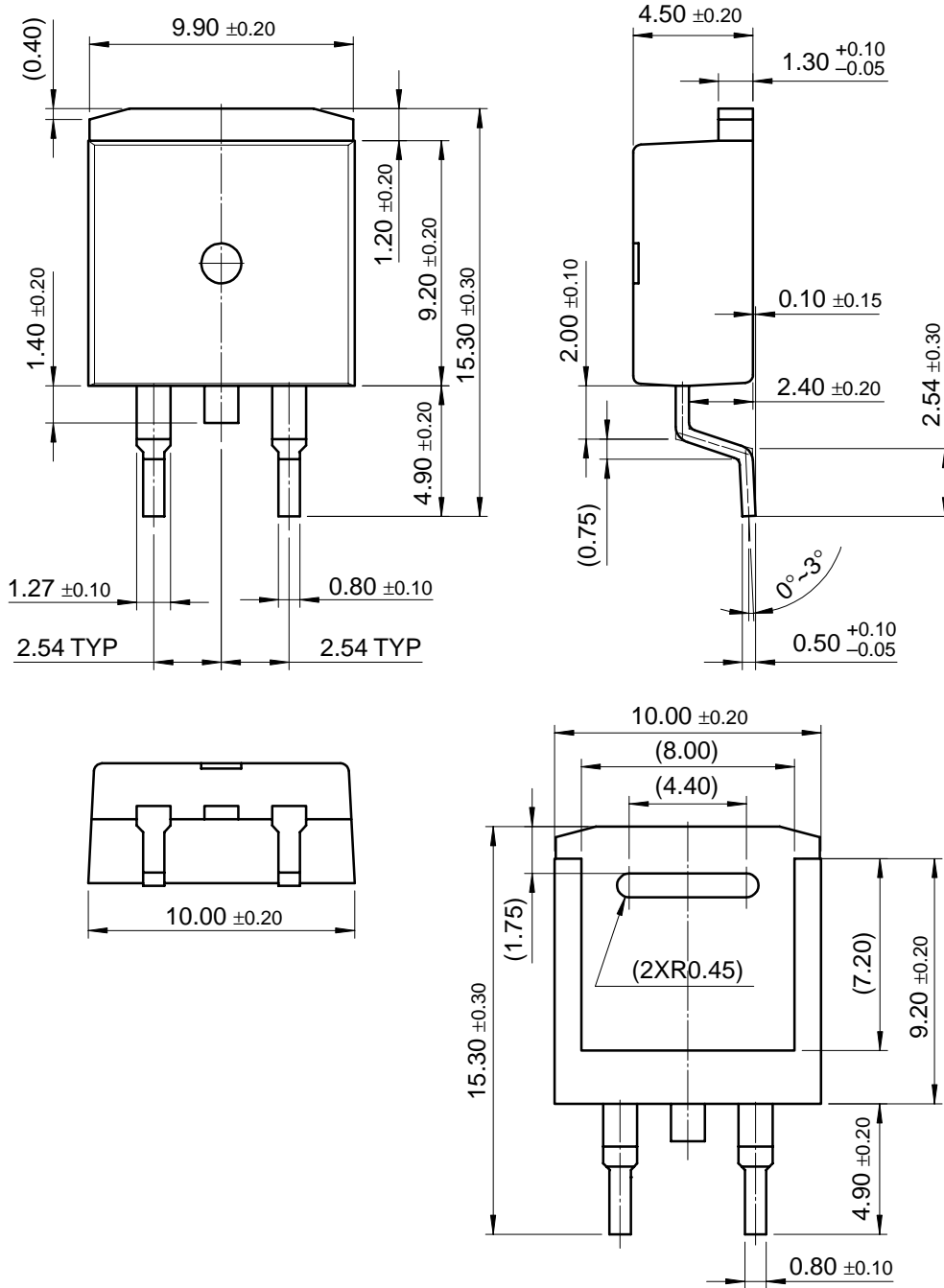


Fig 21. Reverse Recovery Time

Package Dimension

# D<sup>2</sup>-PAK

SGW6N60UFD



Dimensions in Millimeters

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DOMETM	HiSeC™	Power247™	SuperSOT™-3	
EcoSPARK™	I <sup>2</sup> C™	PowerTrench®	SuperSOT™-6	
E <sup>2</sup> CMOS™	ISOPLANAR™	QFET™	SuperSOT™-8	
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